

# Seungjun Lee

## List of Publications by Year in descending order

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papers

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docs citations

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346  
citing authors

#	ARTICLE	IF	CITATIONS
1	In-Place Calibration With Single Measurement in Time-Domain Microwave Breast Imaging. IEEE Antennas and Wireless Propagation Letters, 2017, 16, 206-209.	4.0	4
2	Recent Advances in Microwave Imaging for Breast Cancer Detection. International Journal of Biomedical Imaging, 2016, 2016, 1-26.	3.9	132
3	Verification of in-place calibration for time-domain microwave imaging. , 2016, , .		0
4	Computational modeling of epileptiform activities in medial temporal lobe epilepsy combined with in vitro experiments. Journal of Computational Neuroscience, 2016, 41, 207-223.	1.0	7
5	Switching Time and Stability Evaluation for Writing Operation of STT-MRAM Crossbar Array. IEEE Transactions on Electron Devices, 2016, 63, 3914-3921.	3.0	5
6	A Full Adder Design Using Serially Connected Single-Layer Magnetic Tunnel Junction Elements. IEEE Transactions on Electron Devices, 2008, 55, 890-895.	3.0	16
7	Low-voltage-driven pentacene thin-film transistor with an organic-inorganic nanohybrid dielectric. Applied Physics Letters, 2007, 91, .	3.3	25
8	Pentacene and ZnO hybrid channels for complementary thin-film transistor inverters operating at 2V. Journal of Applied Physics, 2007, 102, .	2.5	32
9	The 3-Bit Gray Counter Based on Magnetic-Tunnel-Junction Elements. IEEE Transactions on Magnetics, 2007, 43, 2677-2679.	2.1	26
10	Magneto-Logic Device Based on a Single-Layer Magnetic Tunnel Junction. IEEE Transactions on Electron Devices, 2007, 54, 2040-2044.	3.0	26
11	A Novel Sensing Circuit for High Speed Synchronous Magneto-Resistive RAM. Japanese Journal of Applied Physics, 2004, 43, 2226-2229.	1.5	0
12	ENERGY-CONSTRAINED VDD HOPPING SCHEME WITH RUN-TIME POWER ESTIMATION FOR LOW-POWER REAL-TIME VLSI SYSTEMS. Journal of Circuits, Systems and Computers, 2002, 11, 601-620.	1.5	2
13	An 0.1- $\mu$ m asymmetric halo by large-angle-tilt implant (AHLATI) MOSFET for high performance and reliability. IEEE Transactions on Electron Devices, 1999, 46, 820-822.	3.0	36